

Philomela Komninou

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

228
papers

2,871
citations

26
h-index

42
g-index

239
ext. papers

3,058
ext. citations

3.1
avg, IF

4.5
L-index

#	Paper	IF	Citations
228	Stacking Fault Manifolds and Structural Configurations of Partial Dislocations in InGaN Epilayers. <i>Physica Status Solidi (B): Basic Research</i> , 2021 , 258, 2170053	1.3	
227	Substitutional synthesis of sub-nanometer InGaN/GaN quantum wells with high indium content. <i>Scientific Reports</i> , 2021 , 11, 20606	4.9	2
226	Ab Initio Study of the Electron-Phonon Coupling in Ultrathin Al Layers. <i>Journal of Low Temperature Physics</i> , 2021 , 203, 180-193	1.3	
225	HRTEM study of microstructure-coercivity relationship in perpendicular Co ₂₅ Pd ₇₅ thin films. <i>Journal of Magnetism and Magnetic Materials</i> , 2021 , 529, 167816	2.8	0
224	Probing the structural role of Cr in stabilized tannery wastes with X-ray absorption fine structure spectroscopy. <i>Journal of Hazardous Materials</i> , 2021 , 402, 123734	12.8	2
223	Understanding the Role of Defects in Silicon Nitride-Based Resistive Switching Memories Through Oxygen Doping. <i>IEEE Nanotechnology Magazine</i> , 2021 , 1-1	2.6	3
222	Large out-of-plane piezoelectric response of wurtzite InN under biaxial strain. <i>Modelling and Simulation in Materials Science and Engineering</i> , 2021 , 29, 065013	2	2
221	Decorated Dislocations against Phonon Propagation for Thermal Management. <i>ACS Applied Energy Materials</i> , 2020 , 3, 2682-2694	6.1	5
220	Effect of Sintering Temperature of Bioactive Glass Nanoceramics on the Hemolytic Activity and Oxidative Stress Biomarkers in Erythrocytes. <i>Cellular and Molecular Bioengineering</i> , 2020 , 13, 201-218	3.9	3
219	The heterogeneous nucleation of threading dislocations on partial dislocations in III-nitride epilayers. <i>Scientific Reports</i> , 2020 , 10, 17371	4.9	6
218	On the applicability of elastic model to very thin crystalline layers. <i>Journal of Physics: Conference Series</i> , 2019 , 1190, 012017	0.3	
217	Effects of ultrathin AlN prelayers on the spontaneous growth of GaN nanowires by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2019 , 514, 89-97	1.6	5
216	Nanospheres and nanoflowers of copper bismuth sulphide (Cu ₃ BiS ₃): Colloidal synthesis, structural, optical and electrical characterization. <i>Journal of Alloys and Compounds</i> , 2019 , 776, 142-148	5.7	14
215	Strong suppression of In desorption from InGaN QW by improved technology of upper InGaN/GaN QW interface. <i>Journal of Crystal Growth</i> , 2019 , 507, 310-315	1.6	2
214	Deformation and fracture in (0001) and (10-10) GaN single crystals. <i>Materials Science and Technology</i> , 2018 , 34, 1531-1538	1.5	4
213	Compositional and strain analysis of In(Ga)N/GaN short period superlattices. <i>Journal of Applied Physics</i> , 2018 , 123, 024304	2.5	8
212	Stabilization of Cr-rich tannery waste in fly ash matrices. <i>Waste Management and Research</i> , 2018 , 36, 818-826	4	4

211	Structural and electronic properties of a-edge dislocations along <1-100> in GaN. <i>Journal of Applied Physics</i> , 2018 , 123, 244301	2.5	4
210	Strain and elastic constants of GaN and InN. <i>Computational Condensed Matter</i> , 2017 , 10, 25-30	1.7	5
209	Investigation of magnetic coupling in FePt/spacer/FePt trilayers. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 445002	3	1
208	Vitrification of incinerated tannery sludge in silicate matrices for chromium stabilization. <i>Waste Management</i> , 2017 , 59, 237-246	8.6	23
207	Ab-initio electronic structure calculations and properties of [SixSn1-k]3N4 ternary nitrides. <i>Thin Solid Films</i> , 2016 , 613, 43-47	2.2	3
206	Ultra-thin epitaxial selenide films: Structure and two-dimensional properties 2016 , 451-452		
205	Structure of short period In(Ga)N/GaN superlattices comprising ultra-thin quantum wells 2016 , 592-593		
204	Ordered structures in III-Nitride ternary alloys. <i>Computational Materials Science</i> , 2016 , 118, 22-31	3.2	8
203	Understanding the effects of Si (111) nitridation on the spontaneous growth and properties of GaN nanowires. <i>Journal of Crystal Growth</i> , 2016 , 442, 8-13	1.6	16
202	The Metalorganic Vapour Phase Epitaxy Growth of AlIBVHeterostructures Observed by Reflection Anisotropy Spectroscopy. <i>Acta Physica Polonica A</i> , 2016 , 129, A-75-A-78	0.6	1
201	Microstructure of glass ceramics synthesized from chromium waste 2016 , 710-711		
200	The influence of structural characteristics on the electronic and thermal properties of GaN/AlN core/shell nanowires. <i>Journal of Applied Physics</i> , 2016 , 119, 074304	2.5	7
199	Selective-area growth of GaN nanowires on SiO ₂ -masked Si (111) substrates by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2016 , 119, 224305	2.5	24
198	Interfacial properties of self-assembled GaN nanowires on pre-processed Al ₂ O ₃ (0001) surfaces. <i>Materials Science in Semiconductor Processing</i> , 2016 , 55, 46-50	4.3	2
197	Energetic, structural and electronic properties of metal vacancies in strained AlN/GaN interfaces. <i>Journal of Physics Condensed Matter</i> , 2015 , 27, 125006	1.8	4
196	Laser-matter interactions, phase changes and diffusion phenomena during laser annealing of plasmonic AlN:Ag templates and their applications in optical encoding. <i>Journal Physics D: Applied Physics</i> , 2015 , 48, 285306	3	6
195	Direct spontaneous growth and interfacial structural properties of inclined GaN nanopillars on r-plane sapphire. <i>Journal of Applied Physics</i> , 2015 , 117, 244302	2.5	1
194	High-quality, large-area MoSe ₂ and MoSe ₂ /Bi ₂ Se ₃ heterostructures on AlN(0001)/Si(111) substrates by molecular beam epitaxy. <i>Nanoscale</i> , 2015 , 7, 7896-905	7.7	107

193	Structural and electronic properties of GaN nanowires with embedded In _x Ga _{1-x} N nanodisks. <i>Journal of Applied Physics</i> , 2015 , 118, 034301	2.5	11
192	Defects, strain relaxation, and compositional grading in high indium content InGaN epilayers grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2015 , 118, 155301	2.5	34
191	Nanostructure and strain properties of core-shell GaAs/AlGaAs nanowires. <i>Semiconductor Science and Technology</i> , 2015 , 30, 114012	1.8	5
190	A study of the piezoelectric properties of semipolar GaN/AlN quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 2296-2303	1.3	2
189	MOVPE prepared InAs/GaAs quantum dots covered by GaAsSb layer with long wavelength emission at 1.8 μ m. <i>Journal of Crystal Growth</i> , 2015 , 414, 167-171	1.6	8
188	Growth of InAs/GaAs quantum dots covered by GaAsSb in multiple structures studied by reflectance anisotropy spectroscopy. <i>Journal of Crystal Growth</i> , 2015 , 414, 156-160	1.6	14
187	Structural and electronic properties of elastically strained InN/GaN quantum well multilayer heterostructures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 289-292		4
186	Influence of laser annealing on the structural properties of sputtered AlN:Ag plasmonic nanocomposites. <i>Journal of Materials Science</i> , 2014 , 49, 3996-4006	4.3	7
185	Thermal oxidation and facet-formation mechanisms of Si nanowires. <i>Physica Status Solidi - Rapid Research Letters</i> , 2014 , 8, 307-311	2.5	1
184	Structural and photoluminescent properties of low temperature InAs buffer layer grown by MOVPE on GaAs substrates. <i>Journal of Crystal Growth</i> , 2014 , 396, 54-60	1.6	
183	Broad compositional tunability of indium tin oxide nanowires grown by the vapor-liquid-solid mechanism. <i>APL Materials</i> , 2014 , 2, 056104	5.7	17
182	Transport properties of metal/semiconductor junctions on n-type InP prepared by electrophoretic deposition of Pt nanoparticles. <i>Semiconductor Science and Technology</i> , 2014 , 29, 045017	1.8	14
181	Misfit dislocation reduction in InGaAs epilayers grown on porous GaAs substrates. <i>Applied Surface Science</i> , 2014 , 306, 89-93	6.7	7
180	Observation of surface Dirac cone in high-quality ultrathin epitaxial Bi ₂ Se ₃ topological insulator on AlN(0001) dielectric. <i>ACS Nano</i> , 2014 , 8, 6614-9	16.7	33
179	Self-annihilation of inversion domains by high energy defects in III-Nitrides. <i>Applied Physics Letters</i> , 2014 , 104, 141914	3.4	5
178	Effect of the lower and upper interfaces on the quality of InAs/GaAs quantum dots. <i>Applied Surface Science</i> , 2014 , 301, 173-177	6.7	10
177	Structural anisotropic properties of a-plane GaN epilayers grown on r-plane sapphire by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2014 , 115, 213506	2.5	15
176	Nanostructure and strain in InGaN/GaN superlattices grown in GaN nanowires. <i>Nanotechnology</i> , 2013 , 24, 435702	3.4	49

175	Growth mechanism and microstructure of low defect density InN (0001) In-face thin films on Si (111) substrates. <i>Journal of Applied Physics</i> , 2013 , 114, 163519	2.5	8
174	Ultrafast pulsed laser deposition of carbon nanostructures: Structural and optical characterization. <i>Applied Surface Science</i> , 2013 , 278, 101-105	6.7	9
173	Structural properties of SnO ₂ nanowires and the effect of donor like defects on its charge distribution. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 226-229	1.6	9
172	Influence of defect characteristics on the nanoindentation response of a-plane GaN thin films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 213-217	1.6	2
171	Structure and interfacial properties of semipolar s-plane (1-101) InN grown on r-plane sapphire. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 199-203	1.6	2
170	Dissociation of the 60° basal dislocation in wurtzite GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 84-88		9
169	Structural and electronic properties of InGa _{0.1} N/GaN nanowires by the use of EELS. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 105-108		1
168	Extended Defects in Semiconductors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 7-9		
167	The 60° basal dislocation in wurtzite GaN: Energetics, electronic and core structures. <i>Computational Materials Science</i> , 2013 , 79, 118-124	3.2	9
166	Si nanostructures grown by picosecond high repetition rate pulsed laser deposition. <i>Applied Surface Science</i> , 2013 , 278, 67-70	6.7	4
165	Electron energy loss near edge structure of In _x Al _{1-x} N alloys. <i>Microelectronic Engineering</i> , 2013 , 112, 198-203	2.5	3
164	Atomic scale morphology, growth behaviour and electronic properties of semipolar {101 $\bar{1}$ 0} GaN surfaces. <i>Journal of Physics Condensed Matter</i> , 2013 , 25, 045008	1.8	2
163	Optical properties of GaN-based nanowires containing a single Al(0.14)Ga(0.86)N/GaN quantum disc. <i>Nanotechnology</i> , 2013 , 24, 125201	3.4	10
162	Nanostructural and electronic properties of polytypes in InN nanocolumns. <i>Journal of Applied Physics</i> , 2013 , 114, 074312	2.5	3
161	Combined vertically correlated InAs and GaAsSb quantum dots separated by triangular GaAsSb barrier. <i>Journal of Applied Physics</i> , 2013 , 114, 174305	2.5	8
160	InGa _{0.1} N/GaN quantum dots as optical probes for the electric field at the GaN/electrolyte interface. <i>Journal of Applied Physics</i> , 2013 , 114, 074313	2.5	4
159	Atomistic Simulation of Undissociated 60° Basal Dislocation in Wurtzite GaN. <i>Modeling and Numerical Simulation of Material Science</i> , 2013 , 03, 11-16	0.7	2
158	Structural properties of semipolar InGa _{0.1} N/GaN quantum dot superlattices grown by plasma-assisted MBE. <i>Microelectronic Engineering</i> , 2012 , 90, 108-111	2.5	6

157	Structure and strain state of polar and semipolar InGaN quantum dots. <i>Applied Surface Science</i> , 2012 , 260, 7-12	6.7	6
156	Morphology and origin of V-defects in semipolar (11 $\bar{2}$ 2) InGaN. <i>Journal of Crystal Growth</i> , 2012 , 339, 1-7	1.6	7
155	Effects of intrasubband coupling on the scattering phases and density of states in a quantum wire. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2012 , 376, 3337-3341	2.3	
154	Optical encoding by plasmon-based patterning: hard and inorganic materials become photosensitive. <i>Nano Letters</i> , 2012 , 12, 259-63	11.5	41
153	Effect of doping on screw threading dislocations in AlN and their role as conductive nanowires. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 484-487		2
152	Structural characterization of InN epilayers grown on r-plane sapphire by plasma-assisted MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 534-537		4
151	Atomistic modeling and HRTEM analysis of misfit dislocations in InN/GaN heterostructures. <i>Applied Surface Science</i> , 2012 , 260, 23-28	6.7	5
150	Reconstructions and electronic structure of (112 $\bar{2}$) and (112 $\bar{2}$) semipolar AlN surfaces. <i>Journal of Applied Physics</i> , 2012 , 112, 033510	2.5	7
149	Internal quantum efficiency of III-nitride quantum dot superlattices grown by plasma-assisted molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2011 , 109, 103501	2.5	54
148	Properties of GaN Nanowires Grown by Molecular Beam Epitaxy. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011 , 17, 878-888	3.8	99
147	Indium adsorption and incorporation mechanisms in AlN. <i>Journal of Materials Science</i> , 2011 , 46, 4377-4383	4.3	4
146	Comparison of Fe and Si doping of GaN: An EXAFS and Raman study. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2011 , 176, 723-726	3.1	9
145	Growth and characterization of polar (0001) and semipolar (11 $\bar{2}$ 2) InGaN/GaN quantum dots. <i>Journal of Crystal Growth</i> , 2011 , 323, 161-163	1.6	9
144	Influence of thermal oxidation on the interfacial properties of ultrathin strained silicon layers. <i>Thin Solid Films</i> , 2011 , 519, 5456-5463	2.2	
143	Effect of edge threading dislocations on the electronic structure of InN. <i>Applied Physics Letters</i> , 2011 , 98, 072103	3.4	22
142	Improved luminescence and thermal stability of semipolar (11-22) InGaN quantum dots. <i>Applied Physics Letters</i> , 2011 , 98, 201911	3.4	18
141	Screw threading dislocations in AlN: Structural and electronic properties of In and O doped material. <i>Journal of Applied Physics</i> , 2011 , 110, 053715	2.5	13
140	Electronic properties and bonding characteristics of AlN:Ag thin film nanocomposites. <i>Journal of Applied Physics</i> , 2011 , 109, 054310	2.5	8

139	Electronic structure of 1/6 $\langle 202 \rangle$ B partial dislocations in wurtzite GaN. <i>Journal of Applied Physics</i> , 2011 , 109, 083511	2.5	15
138	Nonlinear Finite Element and Atomistic Modelling of Dislocations in Heterostructures. <i>Advanced Structured Materials</i> , 2010 , 239-253	0.6	
137	Piezoelectric InAs (211)B quantum dots grown by molecular beam epitaxy: Structural and optical properties. <i>Journal of Applied Physics</i> , 2010 , 108, 103525	2.5	17
136	Bare-eye view at the nanoscale: new visual interferometric multi-indicator (VIMI). <i>ACS Applied Materials & Interfaces</i> , 2010 , 2, 3052-8	9.5	3
135	On the deposition mechanisms and the formation of glassy Cu ₂ S thin films. <i>Journal of Applied Physics</i> , 2010 , 107, 084313	2.5	20
134	Morphology and strain of self-assembled semipolar GaN quantum dots in (112 $\bar{2}$) AlN. <i>Journal of Applied Physics</i> , 2010 , 108, 104304	2.5	20
133	Structure, stability and mechanical performance of AlN:Ag nanocomposite films. <i>Surface and Coatings Technology</i> , 2010 , 204, 1937-1941	4.4	8
132	Direct comparison of catalyst-free and catalyst-induced GaN nanowires. <i>Nano Research</i> , 2010 , 3, 528-536	10	154
131	Crystallization process of thermally treated vitrified EAFD waste. <i>Journal of the European Ceramic Society</i> , 2010 , 30, 2009-2015	6	1
130	Microstructure of N-face InN grown on Si (111) by plasma-assisted MBE using a thin GaN/AlN buffer layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1074-1078	1.6	6
129	Interfacial structure of semipolar AlN grown on m-plane sapphire by MBE. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1637-1640	1.3	12
128	Continuum and Atomistic Modeling of the Mixed Straight Dislocation. <i>International Journal for Multiscale Computational Engineering</i> , 2010 , 8, 331-342	2.4	4
127	Study of interfacial defects induced during the oxidation of ultrathin strained silicon layers. <i>Journal of Applied Physics</i> , 2009 , 105, 114503	2.5	1
126	Mechanism of compositional modulations in epitaxial InAlN films grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2009 , 95, 021913	3.4	46
125	Stranski-Krastanow growth of (112 $\bar{2}$)-oriented GaN/AlN quantum dots. <i>Applied Physics Letters</i> , 2009 , 94, 111901	3.4	14
124	Indium migration paths in V-defects of InAlN grown by metal-organic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2009 , 95, 071905	3.4	60
123	Strain accommodation and interfacial structure of AlN interlayers in GaN. <i>Crystal Research and Technology</i> , 2009 , 44, 1170-1180	1.3	5
122	Magnesium adsorption and incorporation in InN (0001) and surfaces: A first-principles study. <i>Applied Surface Science</i> , 2009 , 255, 8475-8482	6.7	3

121	Silver nanoparticles and graphitic carbon through thermal decomposition of a silver/acetylenedicarboxylic salt. <i>Nanoscale Research Letters</i> , 2009 , 4, 1358-64	5	16
120	Core models of a-edge threading dislocations in wurtzite III(Al,Ga,In)-nitrides. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1931-1935	1.6	12
119	Polar AlN/GaN interfaces: Structures and energetics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1892-1897	1.6	17
118	Energetics of oxygen adsorption and incorporation at InN polar surface: A first-principles study. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S364-S367		2
117	Metal-containing amorphous carbon (a-C:Ag) and AlN (AlN:Ag) metallo-dielectric nanocomposites. <i>Thin Solid Films</i> , 2009 , 518, 1508-1511	2.2	16
116	Effect of AlN interlayers in the structure of GaN-on-Si grown by plasma-assisted MBE. <i>Journal of Crystal Growth</i> , 2009 , 311, 2010-2015	1.6	7
115	Structural role and coordination environment of Fe in Fe ₂ O ₃ /PbO/SiO ₂ /Na ₂ O composite glasses. <i>Journal of Non-Crystalline Solids</i> , 2008 , 354, 105-111	3.9	18
114	Dislocation core investigation by geometric phase analysis and the dislocation density tensor. <i>Journal Physics D: Applied Physics</i> , 2008 , 41, 035408	3	37
113	Effects of Stress-relieving AlN Interlayers in GaN-on-Si Grown by Plasma-assisted Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1068, 1		
112	Step-induced misorientation of GaN grown on r-plane sapphire. <i>Applied Physics Letters</i> , 2008 , 93, 021910	3.4	14
111	Microstructure of defects in InGaN/GaN quantum well heterostructures. <i>Journal of Physics: Conference Series</i> , 2008 , 126, 012048	0.3	2
110	Controlled growth of porous networks in phosphide semiconductors. <i>Journal of Porous Materials</i> , 2008 , 15, 75-81	2.4	5
109	Interface controlled active fracture modes in glass-ceramics. <i>Journal of Materials Science</i> , 2008 , 43, 3954-3959	4.3	2
108	Crystallization of amorphous silicon thin films: comparison between experimental and computer simulation results. <i>Journal of Materials Science</i> , 2008 , 43, 3976-3981	4.3	
107	Study of InN/GaN interfaces using molecular dynamics. <i>Journal of Materials Science</i> , 2008 , 43, 3982-3988	4.3	13
106	Fano effect in quasi-one-dimensional wires with short- or finite-range impurities. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 3813-3817		1
105	Atomic-scale configuration of catalyst particles on GaN nanowires. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 3716-3719		5
104	Electron microscopy investigation of extended defects in a-plane gallium nitride layers grown on r-plane sapphire by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 3748-3751		6

103	Defect characterization and analysis of III-V nanowires grown by Ni-promoted MBE. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2589-2592	1.6	7
102	Strain relaxation in AlN/GaN heterostructures grown by molecular beam epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2569-2572	1.6	9
101	Temperature dependent EXAFS of InN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2611-2614	1.6	4
100	Effect of composition on the bonding environment of In in InAlN and InGaN epilayers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2593-2597	1.6	5
99	Structural properties of ultrathin InGaN/GaN quantum wells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2556-2559	1.6	
98	Micropore modification in InP. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2577-2580	1.6	2
97	Interatomic potential calculations of III(AI, In)N planar defects with a III-species environment approach. <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 1118-1124	1.3	18
96	Residual Strain Variations in MBE-Grown InN Thin Films. <i>Springer Proceedings in Physics</i> , 2008 , 41-44	0.2	
95	Misfit analysis of the InN/GaN interface through HRTEM image simulations 2008 , 651-652		
94	Axial and radial growth of Ni-induced GaN nanowires. <i>Applied Physics Letters</i> , 2007 , 91, 093113	3.4	71
93	Structural characterization of Na ₂ O-CaO-Bi ₂ O ₃ glass ceramics reinforced with electric arc furnace dust. <i>Journal of the European Ceramic Society</i> , 2007 , 27, 2423-2431	6	15
92	On the distribution and bonding environment of Zn and Fe in glasses containing electric arc furnace dust: a mu-XAFS and mu-XRF study. <i>Journal of Hazardous Materials</i> , 2007 , 142, 297-304	12.8	15
91	Atomic core configurations of the -screw basal dislocation in wurtzite GaN. <i>Journal of Crystal Growth</i> , 2007 , 300, 212-216	1.6	13
90	Effects of ion implantation on the mechanical behavior of GaN films. <i>Thin Solid Films</i> , 2007 , 515, 3011-3018	1.8	18
89	3D modelling of misfit networks in the interface region of heterostructures. <i>Journal Physics D: Applied Physics</i> , 2007 , 40, 4084-4091	3	11
88	Strain distribution of thin InN epilayers grown on (0001) GaN templates by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2007 , 90, 061920	3.4	11
87	Structural properties of 10 ⁴ nm thick InN grown on sapphire (0001). <i>Superlattices and Microstructures</i> , 2006 , 40, 246-252	2.8	32
86	High power ultraviolet light emitting diodes based on GaN/AlGaIn quantum wells produced by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2006 , 100, 104506	2.5	19

85	Depth profile of the biaxial strain in a 10 th thick InN (0001) film. <i>Journal of Applied Physics</i> , 2006 , 100, 113516	2.5	8
84	Synthesis, characterization and thermal properties of polymer/magnetite nanocomposites. <i>Nanotechnology</i> , 2006 , 17, 2046-2053	3.4	74
83	On the coordination environment of Fe- and Pb-rich solidified industrial waste: An X-ray absorption and Mössbauer study. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 2933-2942	3.9	5
82	Plasma-Assisted Molecular Beam Epitaxy of III ^V Nitrides 2006 , 107-191		1
81	Topological Analysis of Defects in Nitride Semiconductors 2006 , 319-377		1
80	InN quantum dots grown on GaN (0001) by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 3983-3987		5
79	Structural and optical characterisation of thick InN epilayers grown with a single or two step growth process on GaN(0001). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 162-166	1.6	4
78	Structural properties of quaternary InAlGa ₂ N MQW grown by plasma-assisted MBE. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 2151-2155	1.6	
77	Analysis of partial dislocations in wurtzite GaN using gradient elasticity. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 2161-2166	1.6	20
76	Mixed partial dislocation core structure in GaN by high resolution electron microscopy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 2156-2160	1.6	8
75	Raman and transmission electron microscopy characterization of InN samples grown on GaN/Al ₂ O ₃ by molecular beam epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1588-1593	1.3	7
74	Structure effects on the magnetism of AgCo nanoparticles. <i>Acta Materialia</i> , 2006 , 54, 5251-5260	8.4	24
73	Application of EXAFS for the determination of the crystallization ratio in a series of vitro-ceramic materials containing industrial waste. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006 , 246, 238-243	1.2	6
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